

## Structural variations induced by thermal treatment in lead feldspar ( $\text{PbAl}_2\text{Si}_2\text{O}_8$ )

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### ABSTRACT

Lead feldspar single crystals were annealed at  $T = 1050$  and  $1000$  °C, starting from a disordered metastable configuration ( $\text{PbF}_H$ ,  $Q_{\text{od}} = 0$ ) and from an ordered configuration ( $\text{PbF}_L$ ,  $Q_{\text{od}} = 0.89$ ). Single-crystal data collection and refinement in space group  $I2/c$  show that the degree of Al-Si order increases to  $Q_{\text{od}} = 0.42$  after annealing the disordered  $\text{PbF}_H$  at  $1050$  °C and decreases to  $Q_{\text{od}} = 0.70$  after annealing the ordered  $\text{PbF}_L$  sample at  $1000$  °C. This suggests that the equilibrium  $Q_{\text{od}}$  is between  $0.70$  and  $0.42$  for temperatures between  $1000$  and  $1050$  °C, where anorthite or strontium feldspar are almost completely ordered. A residual in the difference-Fourier map because of positional disorder was observed near the Pb site in all the refined crystals. The average  $y/b_{\text{pb}}$  coordinate changes with increasing Al-Si disorder, as Pb approaches the glide plane. A significant decrease in the intensity of  $b$ -type reflections was consequently observed. A spontaneous strain, with the main axis almost parallel to the  $a$  axis, is associated with Al-Si ordering. Pb polyhedral deformation related with  $Q_{\text{od}}$  accounts for the observed strain. A calibrating equation,  $Q_{\text{od}} = [(8.427(2) - a) / 0.048(3)]^{1/2}$ , has been calculated and applied to the unit-cell parameters obtained from subsequent thermal treatments and from Bruno and Facchinelli (1972) to define the evolution of the  $Q_{\text{od}}$  vs. the treatment temperature. The thermal behavior of the  $Q_{\text{od}}$  could then be bracketed, suggesting  $T_c$  between  $1150$  and  $1200$  °C for the  $I2/c$ - $C2/m$  phase transition induced by the Al-Si order-disorder process.